

Innovation: Optimizing Mission Assurance on a Smallsat Budget

A VORAGO Technologies Focus

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Although cubesats are expected to be created and deployed relatively inexpensively, there are rising expectations about their reliability.

New Cubesats are expected to operate for longer, in more extreme conditions and observe controlled decommissioning. These objectives are difficult to achieve using Commercial Off-The-Shelf (COTS) electronic components that were not designed to operate in a radiation environment. Conversely, specialist rad-hard components are expensive, often unaffordable for a cubesat, or smallsat, budget.

A New Approach to Radiation Hardening

HARDSIL[®] technology was developed to harden standard CMOS devices against the effects of radiation. Because no specialty wafer fab or equipment is required to harden CMOS-based ICs using HARDSIL, it is possible to create chips at a lower cost than up-screening COTS devices. This brings rad-hard performance capability into the budget envelope for cubesats.

When a high-energy radiation particle strikes silicon, it leaves in its wake a stream of electron-hole pairs that should ideally recombine quickly without the stray charge upsetting any nearby transistors. Unfortunately, there is an unfriendly byproduct of building CMOS devices that results in millions of parasitic bipolar transistors being embedded in the silicon just below the transistor active areas.

These parasitic structures resemble thyristors and lay dormant unless they are triggered by an unwanted event

such as a transient that results from a particle strike. *Figure 1* illustrates a side view of a commercial CMOS structure.

There is an NMOS transistor on the left, a PMOS transistor on the right and the circuit diagram of the parasitic bipolar thyristor structure is superimposed on the diagram. If stray charges from a particle strike cause the parasitic transistors to become forward biased, a short circuit will be created from VDD to VSS. This condition is known as latch-up and requires a reset to rectify — in some cases latch-up can destroy the device.

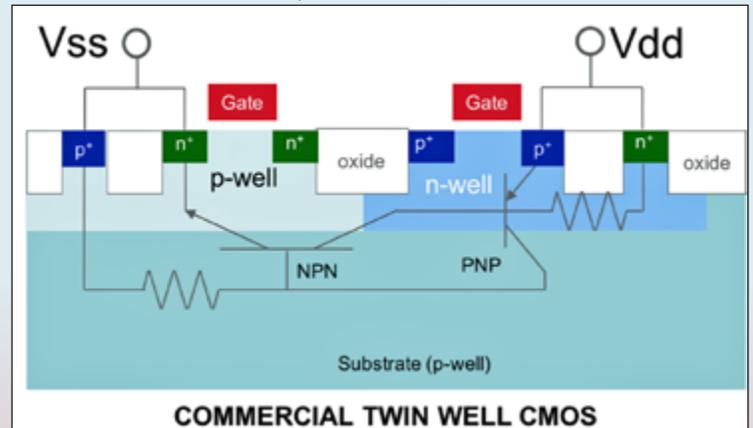


Figure 1. A commercial twin well CMOS device with parasitic thyristor structure.

One of the benefits of HARDSIL technology is to prevent radiation-induced latch-up. This is accomplished by modifying the standard CMOS processing flow in a few simple steps to

